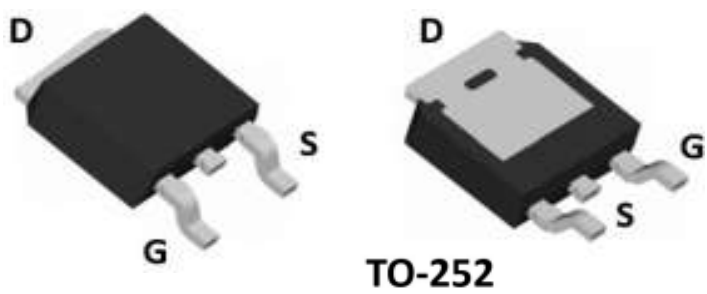
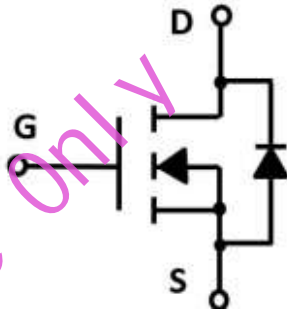


## YC35N06RT

### N-Channel Enhancement Mode Field Effect Transistor

<p><b>Product Summary</b></p> <ul style="list-style-type: none"> <li>● <math>V_{DS}</math> 60V</li> <li>● <math>I_D</math> 35A</li> <li>● <math>R_{DS(ON)}</math>( at <math>V_{GS}=10V</math>) &lt;31mohm</li> <li>● <math>R_{DS(ON)}</math>( at <math>V_{GS}=4.5V</math>) &lt;38mohm</li> <li>● 100% UIS Tested</li> <li>● 100% <math>\nabla V_{DS}</math> Tested</li> </ul>	<p><b>Application</b></p> <ul style="list-style-type: none"> <li>● Power switching application</li> <li>● Hard switched and high frequency circuits</li> <li>● Uninterruptible power supply</li> </ul>	
		

#### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
YC35N06RT	YC35N06RT	TO-252-2L	-	-	-

#### Absolute Maximum Ratings (T<sub>c</sub>=25°C Unless Otherwise Noted)

Parameter	Symbol	Maximum Ratings	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current	$I_D$	T <sub>c</sub> =25°C	35
		T <sub>c</sub> =70°C	27
Pulsed Drain Current	$I_{DM}$	120	A
Maximum Power Dissipation	$P_D$	T <sub>c</sub> =25°C	39
		T <sub>c</sub> =70°C	25
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to 150	°C
Thermal Resistance-Junction to Case *	R <sub>θJC</sub>	3.2	°C/W

\* The device mounted on 1in<sup>2</sup> FR4 board with 2 oz copper

## YC35N06RT

Electrical Characteristics (T<sub>c</sub> =25°C Unless Otherwise Specified)

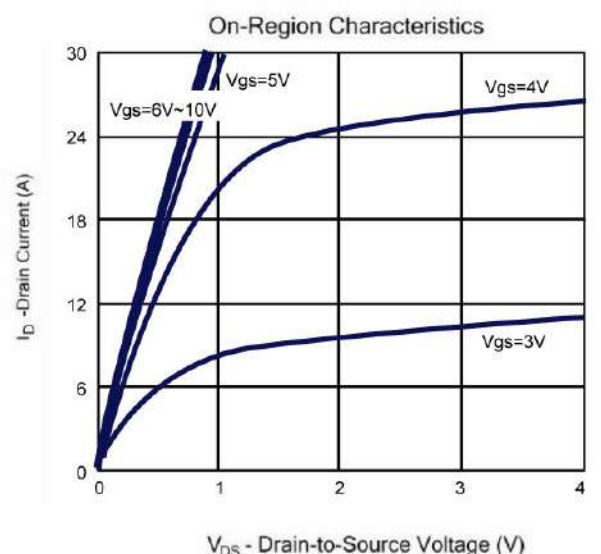
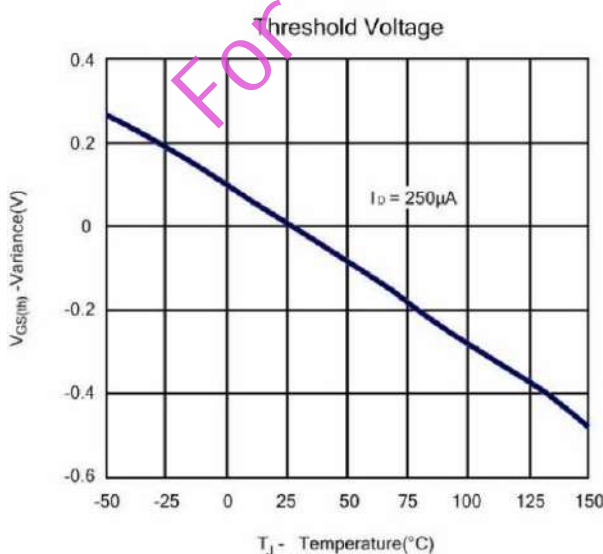
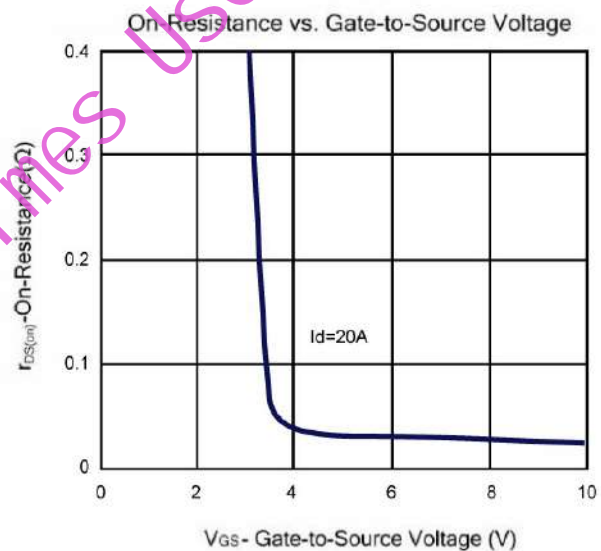
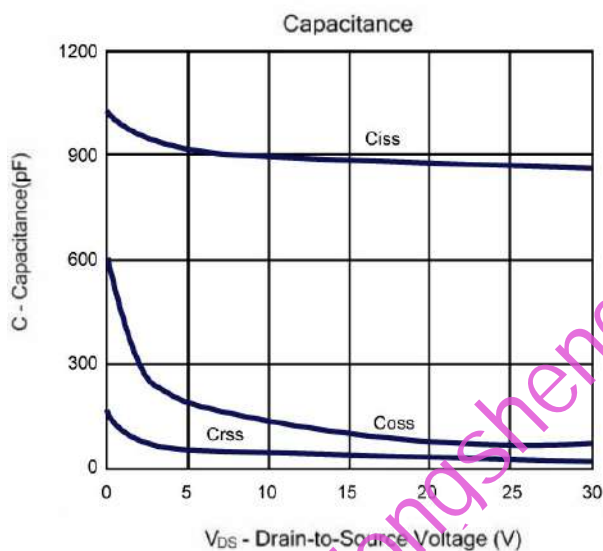
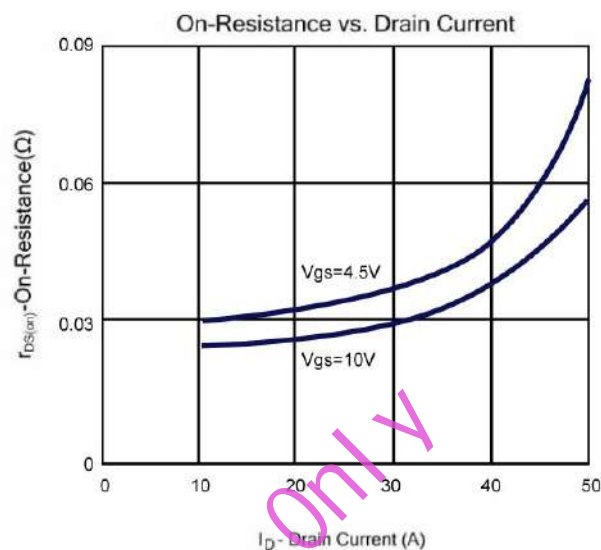
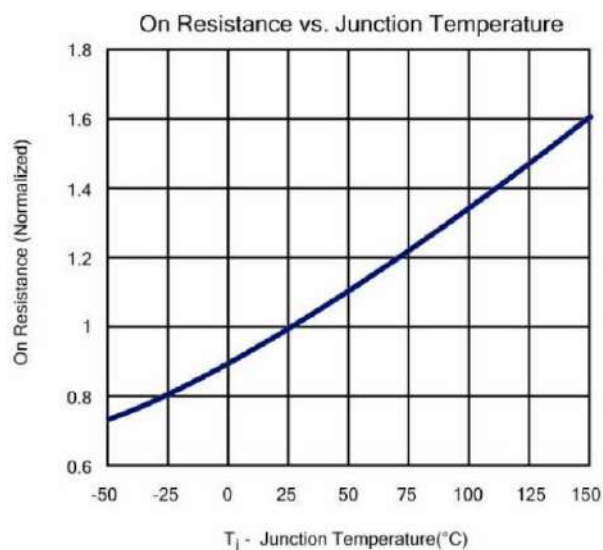
Symbol	Parameter	Limit	Min	Typ	Max	Unit
<b>STATIC</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250 μA	60			V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250 μA	1		3	V
I <sub>GSS</sub>	Gate Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =48V, V <sub>GS</sub> =0V			1	μA
R <sub>DS(ON)</sub>	Drain-Source On-Resistance <sup>a</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A		27	31	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =16A		31	38	
V <sub>SD</sub>	Diode Forward Voltage	I <sub>S</sub> =1A, V <sub>GS</sub> =0V		0.7		V
<b>DYNAMIC</b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =30V, V <sub>GS</sub> =10V, I <sub>D</sub> =20A		23		nC
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> =30V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A		12		
Q <sub>gs</sub>	Gate-Source Charge			4.8		
Q <sub>gd</sub>	Gate-Drain Charge			6.2		
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz		885		pF
C <sub>oss</sub>	Output Capacitance			98		
C <sub>rss</sub>	Reverse Transfer Capacitance			30		
R <sub>g</sub>	Gate-Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz		0.9		Ω
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DS</sub> =30V, R <sub>L</sub> =1.5Ω, V <sub>GEN</sub> =10V, R <sub>G</sub> =3Ω		12		ns
t <sub>r</sub>	Turn-On Rise Time			8		
t <sub>d(off)</sub>	Turn-Off Delay Time			43		
t <sub>f</sub>	Turn-Off Fall Time			4		

Notes: a. Pulse test: pulse width ≤ 300μs, duty cycle ≤ 2%, Guaranteed by design, not subject to production testing.

b. Matsuki Electric/ Force mos reserves the right to improve product design, functions and reliability without notice.

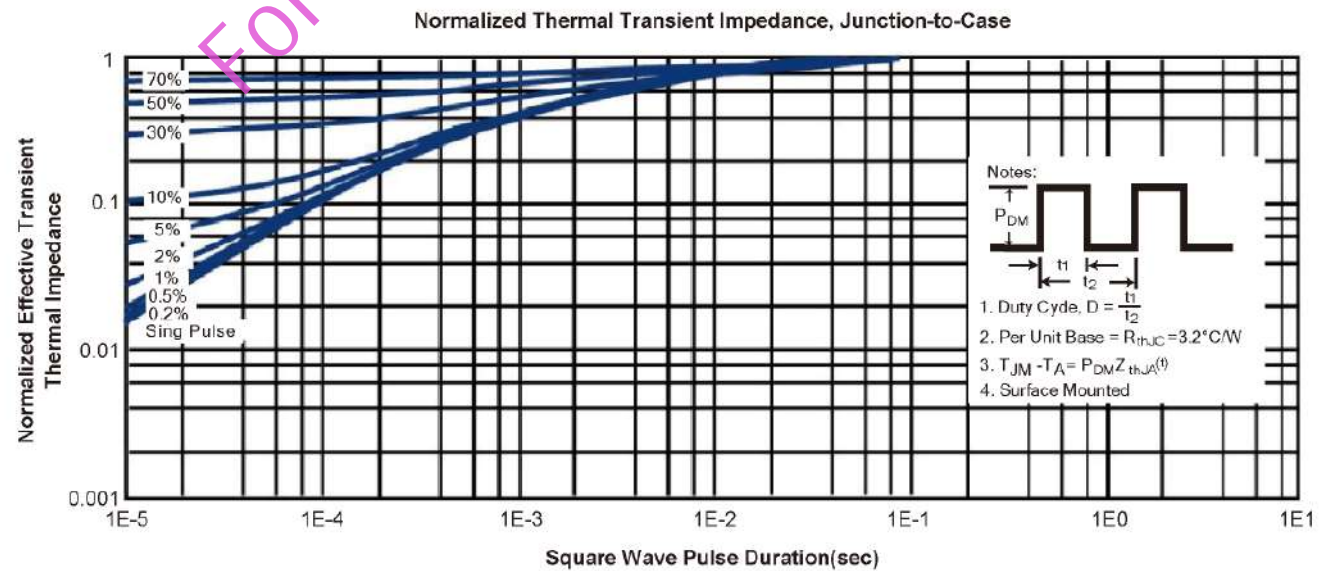
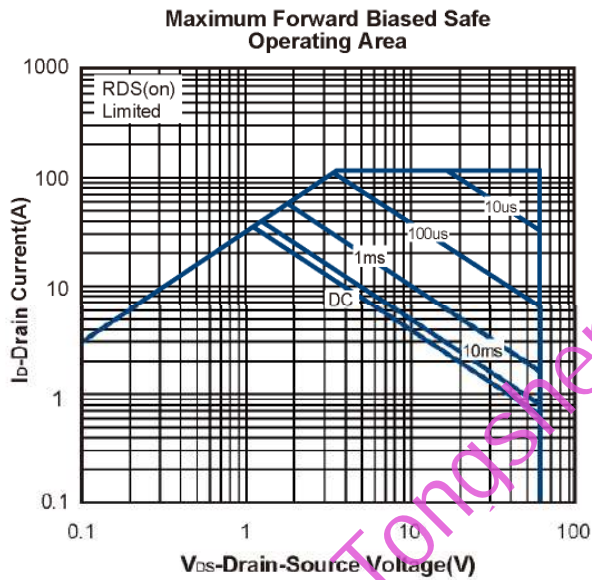
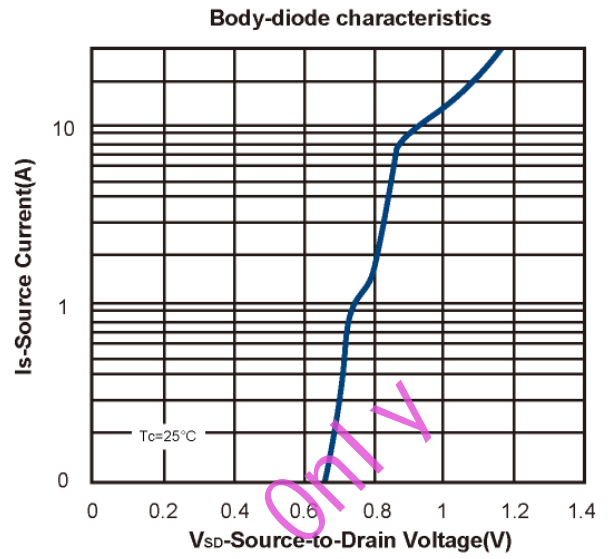
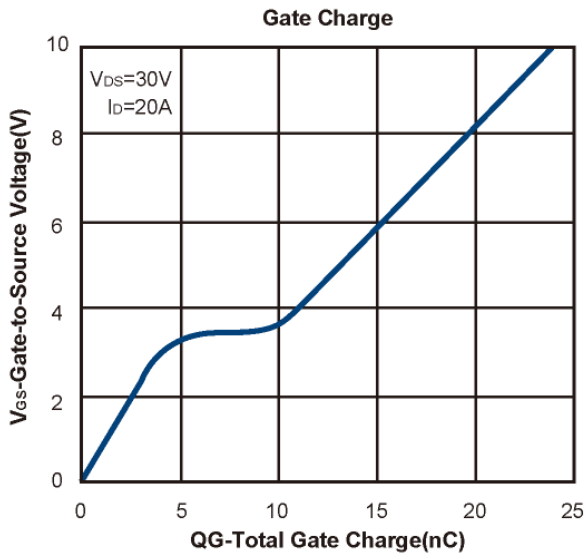
# YC35N06RT

## Typical Characteristics (T<sub>J</sub> =25°C Noted)



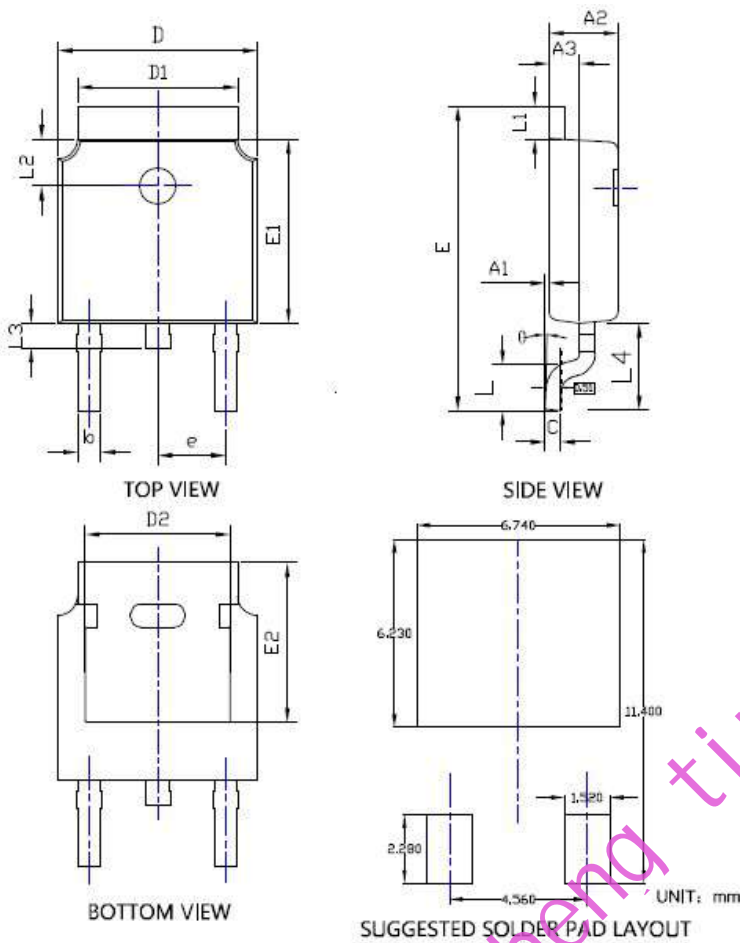
# YC35N06RT

## Typical Characteristics (T<sub>J</sub> =25°C Noted)



# YC35N06RT

## TO-252 Package information



SYMBOL	DIMENSIONS					
	INCHES			Millimeter		
	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
A1	0.000	---	0.008	0.000	---	0.200
A2	0.087	0.091	0.094	2.200	2.300	2.400
A3	0.035	0.039	0.043	0.900	1.000	1.100
b	0.026	0.030	0.034	0.660	0.760	0.860
c	0.018	0.020	0.021	0.460	0.520	0.580
D	0.256	0.260	0.264	6.500	6.600	6.700
D1	0.203	0.209	0.215	5.150	5.300	5.450
D2	0.181	0.185	0.195	4.600	4.800	4.950
E	0.390	0.398	0.406	9.900	10.100	10.300
E1	0.236	0.240	0.244	6.000	6.100	6.200
E2	0.203	0.209	0.215	5.150	5.300	5.450
e	0.090BSC			2.286BSC		
L	0.049	0.059	0.069	1.250	1.500	1.750
L1	0.035	---	0.050	0.900	---	1.270
L2	0.055	---	0.075	1.400	---	1.900
L3	0.240	0.310	0.039	0.600	0.800	1.000
L4	0.114REF			2.900REF		
φ	0*	---	10*	0*	---	10*

NOTE:  
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.  
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.  
 3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

## YC35N06RT

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